



NTMS4P01R2 Information



For Reference Only

Part Number NTMS4P01R2
Manufacturer ON Semiconductor

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 12V 3.4A 8-SOIC **Package** 8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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NTMS4P01R2 Specifications

Manufacturer Part Number NTMS4P01R2 Manufacturer ON Semiconductor Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.15V @ 250µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1850pF @ 9.6V Vgs (Max) ± 10V FET Feature - Power Dissipation (Max) 790mW (Ta) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackage8-SOIC (0.154", 3.90mm Width)Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	NTMS4P01R2
Package 8-SOIC (0.154", 3.90mm Width) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 12V Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.15V @ 250μA Gate Charge (Qg) (Max) @ Vgs 35nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1850pF @ 9.6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) 790mW (Ta) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer	ON Semiconductor
Package8-SOIC (0.154", 3.90mm Width)Series-FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Category	Discrete Semiconductor Products
Series - Channel P-Channel MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 3.4A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1.15V @ 250µA Gate Charge (Qg) (Max) @ Vgs 1850pF @ 9.6V Input Capacitance (Ciss) (Max) @ Vds 1850pF @ 9.6V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature - 55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Package	8-SOIC (0.154", 3.90mm Width)
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Series	-
Drain to Source Voltage (Vdss)12VCurrent - Continuous Drain (Id) @ 25°C3.4A (Ta)Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 2.5V, 4.5V Vgs(th) (Max) @ Id 1.15V @ 250µA Gate Charge (Qg) (Max) @ Vgs 35nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1850pF @ 9.6V Vgs (Max) ±10V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)2.5V, 4.5VVgs(th) (Max) @ Id1.15V @ 250μAGate Charge (Qg) (Max) @ Vgs35nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds1850pF @ 9.6VVgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	12V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs 35nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 1850pF @ 9.6V Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 1.15V @ 250μA 1.15	Current - Continuous Drain (Id) @ 25°C	3.4A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Jemperature Surface Mount Supplier Device Package Package / Case 35nC @ 4.5V 1850pF @ 9.6V 1850pW (Ta) 790mW (Ta) 45 mOhm @ 4.5A, 4.5V Operating Temperature Surface Mount Supplier Device Package 8-SOIC Package / Case	Drive Voltage (Max Rds On, Min Rds On)	2.5V, 4.5V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	1.15V @ 250μA
Vgs (Max)±10VFET Feature-Power Dissipation (Max)790mW (Ta)Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	Gate Charge (Qg) (Max) @ Vgs	35nC @ 4.5V
FET Feature - Power Dissipation (Max) 790mW (Ta) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	1850pF @ 9.6V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 45 mOhm @ 4.5A, 4.5V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs (Max)	±10V
Rds On (Max) @ Id, Vgs45 mOhm @ 4.5A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOICPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	790mW (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	45 mOhm @ 4.5A, 4.5V
Supplier Device Package 8-SOIC Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SOIC
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

NTMS4P01R2 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

NTMS4P01R2 Payment Methods



















NTMS4P01R2 Shipping Methods













If you have any question about NTMS4P01R2, please do not hesitate to contact us!

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